Absolute Maximum Ratings

Stresses beyond the limits listed below may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

V _S	0V to 6V
V _{IN}	$-V_S$ - 0.5V to $+V_S$ +0.5V
Continuous Output Current	40mA to +40mA

Operating Conditions

Supply Voltage Range	2.5 to 5.5V
Operating Temperature Range	40°C to 125°C
Junction Temperature	150°C
Storage Temperature Range	65°C to 150°C
Lead Temperature (Soldering, 10s)	260°C

Package Thermal Resistance

θ _{JA} (SOIC-8)	150°C/W
θ _{JA} (MSOP-8)	200°C/W
θ _{JA} (SOIC-14)	90°C/W
θ _{JA} (TSSOP-14)	100°C/W
Package thermal resistance ($\theta_{\mbox{\scriptsize JA}}\mbox{\scriptsize)},$ JEDEC statest boards, still air.	andard, multi-layer

ESD Protection

CLC2011, CLC4011 (HBM)	2kV
ESD Rating for HBM (Human Body Model).	

Electrical Characteristics at +2.7V

 $T_A=25^{\circ}C,\,V_S=+2.7V,\,R_f=R_g=5k\Omega,\,R_L=10k\Omega\;to\;V_S/2;\,G=2;\,unless\;otherwise\;noted.$

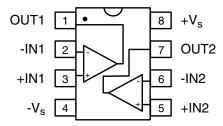
Symbol	Parameter	Conditions Min		Тур	Max	Units		
Frequency	Frequency Domain Response							
UGBW _{SS}	Unity Gain -3dB Bandwidth	$G = +1, V_{OUT} = 0.02V_{pp}$		4.9		MHz		
BW _{SS}	-3dB Bandwidth	$G = +2, V_{OUT} = 0.2V_{pp}$		3.2		MHz		
BW _{LS}	Large Signal Bandwidth	$G = +2$, $V_{OUT} = 2V_{pp}$		1.4		MHz		
GBWP	Gain Bandwidth Product	$G = +11, V_{OUT} = 0.2V_{pp}$		2.5		MHz		
Time Doma	in Response		<u>'</u>			,		
t _R , t _F	Rise and Fall Time	V _{OUT} = 1V step; (10% to 90%)		163		ns		
t _S	Settling Time to 0.1%	V _{OUT} = 1V step		500		ns		
OS	Overshoot	V _{OUT} = 1V step		<1		%		
SR	Slew Rate	1V step		5.3		V/µs		
Distortion/N	loise Response		'			,		
HD2	2nd Harmonic Distortion	$10kHz$, $V_{OUT} = 1V_{pp}$		-72		dBc		
HD3	3rd Harmonic Distortion	10kHz, V _{OUT} = 1V _{pp}		-72		dBc		
THD	Total Harmonic Distortion	$10kHz, V_{OUT} = 1V_{pp}$		0.03		%		
e _n	Input Voltage Noise	>10kHz		21		nV/√Hz		
		Channel to Channel, V _{OUT} = 2V _{pp} , f = 10kHz		82		dB		
X _{TALK}	Crosstalk	Channel to Channel, V _{OUT} = 2V _{pp} , f = 50kHz		74		dB		
DC Perform	ance		<u>'</u>			,		
V _{IO}	Input Offset Voltage			0.5		mV		
d _{VIO}	Average Drift			5		μV/°C		
I _B	Input Bias Current			90		nA		
dl _B	Average Drift			32		pA/°C		
PSRR	Power Supply Rejection Ratio	DC	55	83		dB		
A _{OL}	Open Loop Gain	$V_{OUT} = V_S / 2$		90		dB		
Is	Supply Current	per channel		136		μA		
Input Chara	cteristics		'					
R _{IN}	Input Resistance	Non-inverting		12		ΜΩ		
C _{IN}	Input Capacitance			2		pF		
CMIR	Common Mode Input Range			-0.25 to 2.95		V		
CMRR	Common Mode Rejection Ratio	DC		81		dB		
Output Cha	racteristics							
		$R_L = 10$ kΩ to V_S / 2		0.02 to 2.68		V		
V _{OUT}	Output Voltage Swing	$R_L = 1k\Omega$ to $V_S / 2$		0.05 to 2.63		V		
		$R_L = 200\Omega$ to $V_S / 2$		0.11 to 2.52		V		
I _{OUT}	Output Current			±30		mA		

Electrical Characteristics at +5V

 $T_A=25^{\circ}C,\,V_S=+5V,\,R_f=R_g=5k\Omega,\,R_L=10k\Omega \text{ to }V_S/2;\,G=2; \text{unless otherwise noted}.$

	Symbol	Parameter	Conditions Min		Тур	Max	Units		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Frequency I	Frequency Domain Response							
BWLs	UGBW _{SS}	Unity Gain -3dB Bandwidth	$G = +1, V_{OUT} = 0.02V_{pp}$		4.3		MHz		
Gain Bandwidth Product G = +11, V_OUT = 0.2V_pp	BW _{SS}	-3dB Bandwidth	$G = +2, V_{OUT} = 0.2V_{pp}$		3.0		MHz		
Time Domain Response Fig. 1 Rise and Fall Time Vour = 1V step; (10% to 90%) 110 ns ns Ns Ns Settling Time to 0.1% Vour = 2V step 470 ns Ns Ns Ns Ns Ns Ns Ns	BW _{LS}	Large Signal Bandwidth	$G = +2$, $V_{OUT} = 2V_{pp}$		2.3		MHz		
t _R , t _F Rise and Fall Time V _{OUT} = 1V step; (10% to 90%) 1110 ns t _S Settling Time to 0.1% V _{OUT} = 2V step 470 ns OS Overshoot V _{OUT} = 1V step 470 ns OS Overshoot V _{OUT} = 1V step 470 % SR Siew Rate 2V step 9 V/µs Distortion/Noise Response V V V V HD2 2nd Harmonic Distortion 10kHz, V _{OUT} = 1V _{pp} -75 dBc HD3 3rd Harmonic Distortion 10kHz, V _{OUT} = 1V _{pp} 0.03 % en Input Voltage Noise >10kHz 22 nV//Hz en Input Voltage Noise >10kHz 22 nV//Hz XTALK Crosstalk Channel to Channel, V _{OUT} = 2V _{pp} , f = 10kHz 82 aB DC Performance VIO Input Offset Voltage 8 1.5 8 mV ViO Nort Offset Voltage 8 1.5 8 mV ViO	GBWP	Gain Bandwidth Product			2.5		MHz		
ts Settling Time to 0.1% Vour = 2V step 470 ns OS Overshoot Vour = 1V step <1	Time Doma	in Response							
OS Overshoot Vout = 1V step Siew Rate 2V step 9 V/µs	t _R , t _F	Rise and Fall Time	V _{OUT} = 1V step; (10% to 90%)		110		ns		
Sign Sign Rate 2V step 9 V/μs	t _S	Settling Time to 0.1%	V _{OUT} = 2V step		470		ns		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	OS	Overshoot	V _{OUT} = 1V step		<1		%		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	SR	Slew Rate	2V step		9		V/µs		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Distortion/N	oise Response							
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	HD2	2nd Harmonic Distortion	10kHz, V _{OUT} = 1V _{pp}		-73		dBc		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	HD3	3rd Harmonic Distortion			-75		dBc		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	THD	Total Harmonic Distortion	$10kHz$, $V_{OUT} = 1V_{pp}$		0.03		%		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	e _n	Input Voltage Noise	>10kHz		22		nV/√Hz		
	V	Out and all	Channel to Channel, V _{OUT} = 2V _{pp} , f = 10kHz		82		dB		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	XTALK	Crosstalk	Channel to Channel, V _{OUT} = 2V _{pp} , f = 50kHz		74		dB		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	DC Perform	ance		•					
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	V _{IO}	Input Offset Voltage		-8	1.5	8	mV		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	d _{VIO}	Average Drift			15		μV/°C		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I _B	Input Bias Current			90	450	nA		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	dl _B	Average Drift			40		pA/°C		
$\begin{tabular}{ c c c c c c c c c c } \hline I_S & Supply Current & per channel & 160 & 235 & μA \\ \hline Input Characteristics & & & & & \\ \hline Input Characteristics & & & & & \\ \hline R_{IN} & Input Resistance & Non-inverting & 12 & $M\Omega$ \\ \hline C_{IN} & Input Capacitance & 2 & pF \\ \hline CMIR & Common Mode Input Range & $-0.25\ to 5.25 & V \\ \hline CMRR & Common Mode Rejection Ratio & DC & 58 & 80 & dB \\ \hline Output Characteristics & & & & & \\ \hline V_{OUT} & Output Voltage Swing & & & & & & \\ \hline R_L = 10k\Omega\ to\ V_S/2 & & & & & & & \\ \hline R_L = 10k\Omega\ to\ V_S/2 & & & & & & & \\ \hline R_L = 200\Omega\ to\ V_S/2 & & & & & & & \\ \hline R_L = 200\Omega\ to\ V_S/2 & & & & & & \\ \hline R_L = 200\Omega\ to\ V_S/2 & & & & & & \\ \hline \end{tabular} $	PSRR	Power Supply Rejection Ratio	DC	55	85		dB		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	A _{OL}	Open Loop Gain	$V_{OUT} = V_S / 2$		80		dB		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I _S	Supply Current	per channel		160	235	μΑ		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Input Chara	cteristics							
	R _{IN}	Input Resistance	Non-inverting		12		ΜΩ		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	C _{IN}	Input Capacitance			2		pF		
$V_{OUT} \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	CMIR	Common Mode Input Range					V		
$V_{OUT} \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	CMRR	Common Mode Rejection Ratio	DC	58	80		dB		
$V_{OUT} \qquad \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Output Cha	racteristics							
$R_L = 18\Omega \text{ to V}_S / 2$ 4.9 V $R_L = 200\Omega \text{ to V}_S / 2$ 0.14 to 4.67 V			$R_L = 10k\Omega$ to $V_S / 2$	0.08 to 4.92			V		
$H_{L} = 200\Omega \text{ to V}_{S}/2 $ 4.67	V_{OUT}	Output Voltage Swing	$R_L = 1k\Omega$ to $V_S / 2$				V		
I _{OUT} Output Current ±35 mA			$R_L = 200\Omega$ to $V_S / 2$				V		
	I _{OUT}	Output Current			±35		mA		

CLC2011 Pin Configurations SOIC-8 / MSOP-8

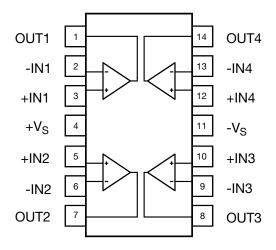


CLC2011 Pin Assignments

SOIC-8 / MSOP-8

Pin No.	Pin Name	Description	
1	OUT1	Output, channel 1	
2	-IN1	Negative input, channel 1	
3	+IN1	Positive input, channel 1	
4	-V _S	Negative supply	
5	+IN2	Positive input, channel 2	
6	-IN2	Negative input, channel 2	
7	OUT2	Output, channel 2	
8	+V _S	Positive supply	

CLC4011 Pin Configuration SOIC-14 / TSSOP-14



CLC4011 Pin Assignments

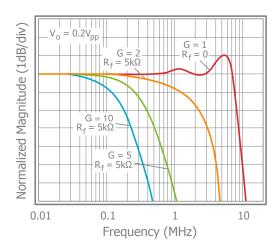
SOIC-14/TSSOP-14

Pin No.	Pin Name	Description	
1	OUT1	Output, channel 1	
2	-IN1	Negative input, channel 1	
3	+IN1	Positive input, channel 1	
4	+V _S	Positive supply	
5	+IN2	Positive input, channel 2	
6	-IN2	Negative input, channel 2	
7	OUT2	Output, channel 2	
8	OUT3	Output, channel 3	
9	-IN3	Negative input, channel 3	
10	+IN3	Positive input, channel 3	
11	-V _S	Negative supply	
12	+IN4	Positive input, channel 4	
13	-IN4	Negative input, channel 4	
14	OUT4	Output, channel 4	

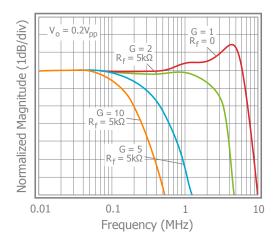
Typical Performance Characteristics

 T_A = 25°C, V_S = +2.7V, R_f = R_g = 5k $\Omega,~R_L$ = 10k Ω to $V_S/2;~G$ = 2; unless otherwise noted.

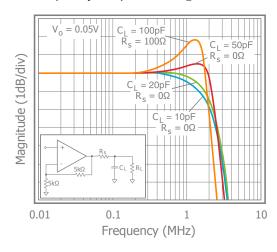
Non-Inverting Frequency Response at $V_S = 5V$



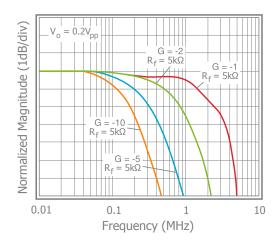
Non-Inverting Frequency Response at V_S = 2.7V



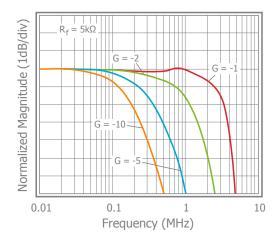
Frequency Response vs CL



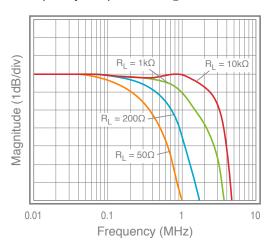
Inverting Frequency Response at $V_S = 5V$



Inverting Frequency Response at V_S = 2.7V



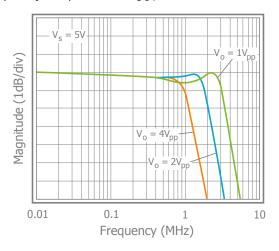
Frequency Response vs RL



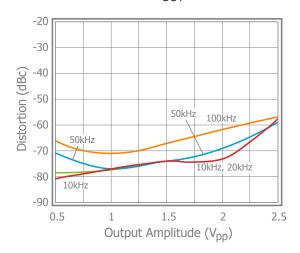
Typical Performance Characteristics

 $T_A = 25^{\circ}C$, $V_S = +2.7V$, $R_f = R_g = 5k\Omega$, $R_L = 10k\Omega$ to $V_S/2$; G = 2; unless otherwise noted.

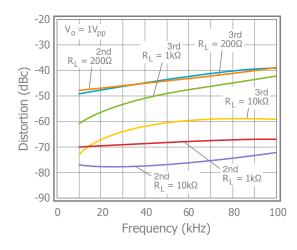
Frequency Response vs. VOUT



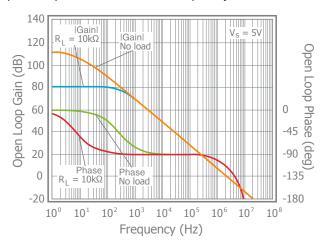
2nd Harmonic Distortion vs V_{OUT}



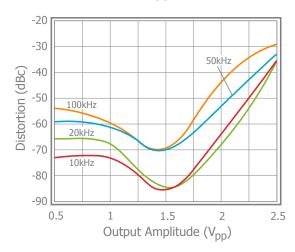
2nd & 3rd Harmonic Distortion at $V_S = 2.7V$



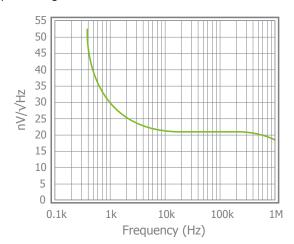
Open Loop Gain & Phase vs. Frequency



3rd Harmonic Distortion vs VOUT



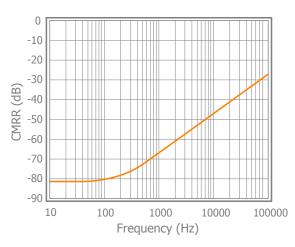
Input Voltage Noise



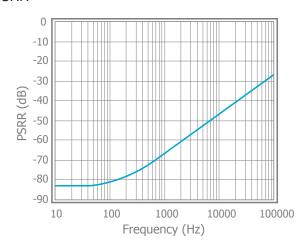
Typical Performance Characteristics

 $T_A = 25^{\circ}C$, $V_S = +2.7V$, $R_f = R_g = 5k\Omega$, $R_L = 10k\Omega$ to $V_S/2$; G = 2; unless otherwise noted.

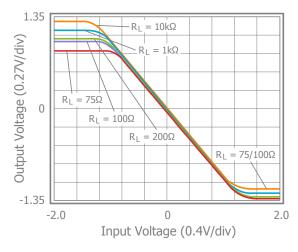
CMRR



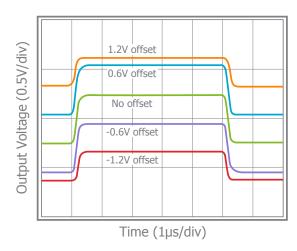
PSRR



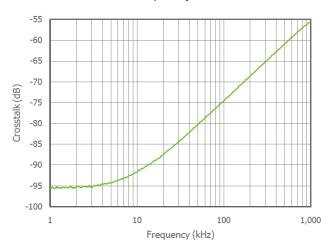
Output Swing vs. Load



Pulse Response vs. Common Mode Voltage



Crosstalk vs. Frequency



Application Information

General Description

The CLCx011 family of amplifiers are single supply, general purpose, voltage-feedback amplifiers. They are fabricated on a complimentary bipolar process, feature a rail-to-rail input and output, and are unity gain stable.

Basic Operation

Figures 1, 2, and 3 illustrate typical circuit configurations for non-inverting, inverting, and unity gain topologies for dual supply applications. They show the recommended bypass capacitor values and overall closed loop gain equations. Figure 4 shows the typical non-inverting gain circuit for single supply applications.

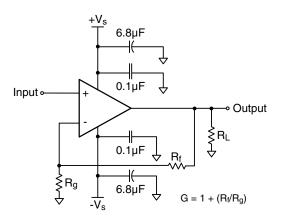


Figure 1: Typical Non-Inverting Gain Circuit

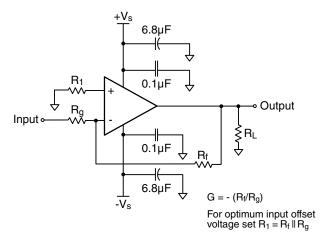


Figure 2: Typical Inverting Gain Circuit

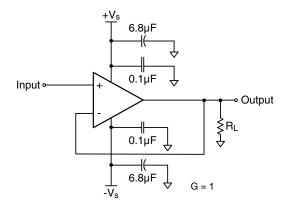


Figure 3: Unity Gain Circuit

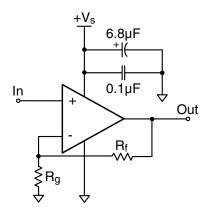


Figure 4: Single Supply Non-Inverting Gain Circuit

Power Dissipation

Power dissipation should not be a factor when operating under the stated $10k\Omega$ load condition. However, applications with low impedance, DC coupled loads should be analyzed to ensure that maximum allowed junction temperature is not exceeded. Guidelines listed below can be used to verify that the particular application will not cause the device to operate beyond it's intended operating range.

Maximum power levels are set by the absolute maximum junction rating of 150°C. To calculate the junction temperature, the package thermal resistance value Theta_JA (θ_{JA}) is used along with the total die power dissipation.

$$T_{Junction} = T_{Ambient} + (\theta_{JA} \times P_D)$$

Where T_{Ambient} is the temperature of the working environment.

In order to determine P_D , the power dissipated in the load needs to be subtracted from the total power delivered by the supplies.

$$P_D = P_{supply} - P_{load}$$

Supply power is calculated by the standard power equation.

$$P_{\text{supply}} = V_{\text{supply}} \times I_{\text{RMSsupply}}$$

$$V_{\text{supply}} = V_{\text{S-}} + V_{\text{S-}}$$

Power delivered to a purely resistive load is:

$$P_{load} = ((V_{load})_{RMS^2})/Rload_{eff}$$

The effective load resistor (Rload $_{\rm eff}$) will need to include the effect of the feedback network. For instance, Rload $_{\rm eff}$ in Figure 3 would be calculated as:

$$R_L \parallel (R_f + R_g)$$

These measurements are basic and are relatively easy to perform with standard lab equipment. For design purposes however, prior knowledge of actual signal levels and load impedance is needed to determine the dissipated power. Here, P_D can be found from

Quiescent power can be derived from the specified I_S values along with known supply voltage, V_{supply} . Load power can be calculated as above with the desired signal amplitudes using:

$$(V_{load})_{RMS} = V_{peak} / \sqrt{2}$$

$$(I_{load})_{RMS} = (V_{load})_{RMS} / Rload_{eff}$$

The dynamic power is focused primarily within the output stage driving the load. This value can be calculated as:

$$P_{Dvnamic} = (V_{S+} - V_{load})_{RMS} \times (I_{load})_{RMS}$$

Assuming the load is referenced in the middle of the power rails or $V_{\text{supply}}/2$.

The CLC2011 is short circuit protected. However, this may not guarantee that the maximum junction temperature (+150°C) is not exceeded under all conditions. Figure 5 shows the maximum safe power dissipation in the package vs. the ambient temperature for the packages available.

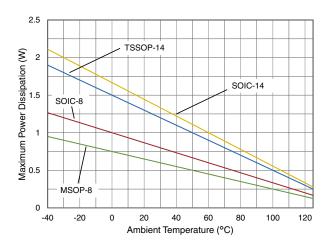


Figure 5. Maximum Power Derating

Input Common Mode Voltage

The common mode input range extends to 250mV below ground and to 250mV above Vs, in single supply operation. Exceeding these values will not cause phase reversal. However, if the input voltage exceeds the rails by more than 0.5V, the input ESD devices will begin to conduct. The output will stay at the rail during this overdrive condition. If the absolute maximum input voltage (700mV beyond either rail) is exceeded, externally limit the input current to ±5mA as shown in Figure 6.

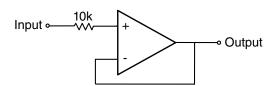


Figure 6. Circuit for Input Current Protection

Driving Capacitive Loads

Increased phase delay at the output due to capacitive loading can cause ringing, peaking in the frequency response, and possible unstable behavior. Use a series resistance, $R_{S},$ between the amplifier and the load to help improve stability and settling performance. Refer to Figure 7.

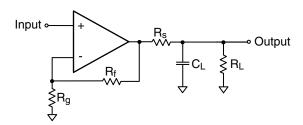


Figure 7. Addition of R_S for Driving Capacitive Loads

Table 1 provides the recommended $R_{\rm S}$ for various capacitive loads. The recommended $R_{\rm S}$ values result in approximately <1dB peaking in the frequency response. The Frequency Response vs. CL plot, on page 6, illustrates the response of the CLCx011.

C _L (pF)	R _S (Ω)	-3dB BW (MHz)
10pF	0	2.2
20pF	0	2.4
50pF	0	2.5
100pF	100	2

Table 1: Recommended R_S vs. C_L

For a given load capacitance, adjust R_S to optimize the tradeoff between settling time and bandwidth. In general, reducing R_S will increase bandwidth at the expense of additional overshoot and ringing.

Overdrive Recovery

An overdrive condition is defined as the point when either one of the inputs or the output exceed their specified voltage range. Overdrive recovery is the time needed for the amplifier to return to its normal or linear operating point. The recovery time varies, based on whether the input or output is overdriven and by how much the range is exceeded. The CLCx011 will typically recover in less than 50ns from an overdrive condition. Figure 8 shows the CLC2011 in an overdriven condition.

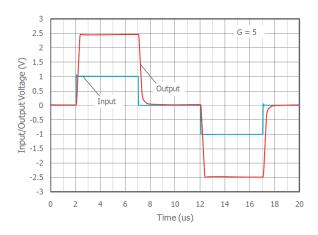


Figure 8: Overdrive Recovery

Layout Considerations

General layout and supply bypassing play major roles in high frequency performance. Resurgent has evaluation boards to use as a guide for high frequency layout and as an aid in device testing and characterization. Follow the steps below as a basis for high frequency layout:

- Include 6.8µF and 0.1µF ceramic capacitors for power supply decoupling
- Place the 6.8µF capacitor within 0.75 inches of the power pin
- Place the 0.1µF capacitor within 0.1 inches of the power pin
- Remove the ground plane under and around the part, especially near the input and output pins to reduce parasitic capacitance
- Minimize all trace lengths to reduce series inductances

Refer to the evaluation board layouts below for more information.

Evaluation Board Information

The following evaluation boards are available to aid in the testing and layout of these devices:

Evaluation Board #	Products
CEB006	CLC2011 in SOIC
CEB010	CLC2011 in MSOP
CEB019	CLC4011 in TSSOP
CEB018	CLC4011 in SOIC

Evaluation Board Schematics

Evaluation board schematics and layouts are shown in Figures 9-16 These evaluation boards are built for dual-supply operation. Follow these steps to use the board in a single-supply application:

- 1. Short -V_S to ground.
- Use C3 and C4, if the -V_S pin of the amplifier is not directly connected to the ground plane.

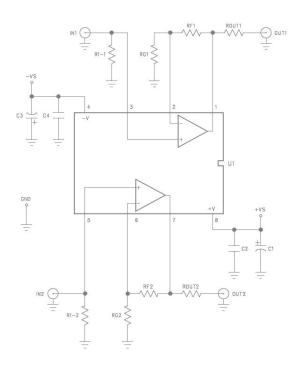


Figure 9. CEB006 & CEB010 Schematic

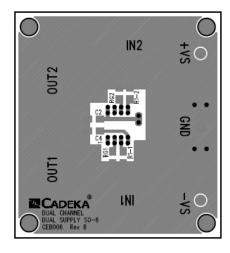


Figure 10. CEB006 Top View

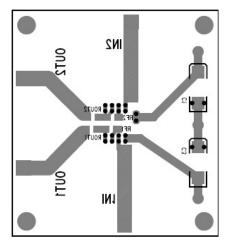


Figure 11. CEB006 Bottom View

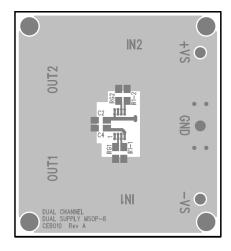


Figure 12. CEB010 Top View

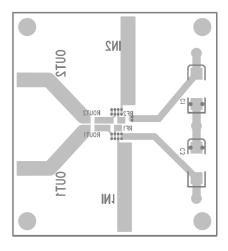


Figure 13. CEB010 Bottom View

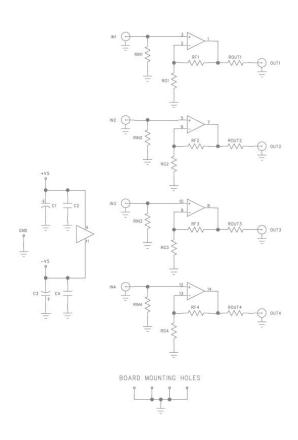


Figure 14. CEB018 Schematic

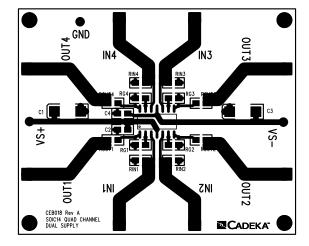


Figure 15. CEB018 Top View

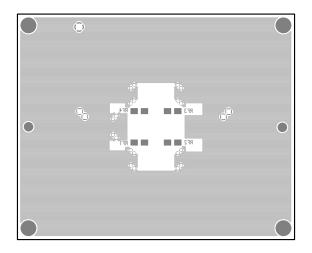
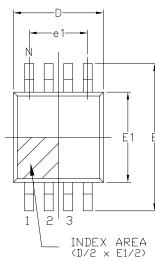


Figure 16. CEB018 Bottom View

Mechanical Dimensions MSOP-8

Top View





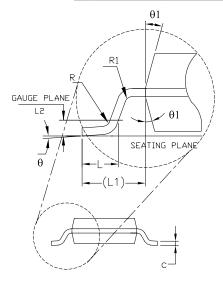
A A1 A2

e b b Side View

8 Pin MSOP JEDEC MO-187 Variation AA DIMENSIONS IN MM (Control Unit) DIMENSIONS IN INCH SYMBOLS MIN NOM MAX MIN NOM MAX
 1.10
 0.0043

 0.00
 0.15
 0.000
 0.006

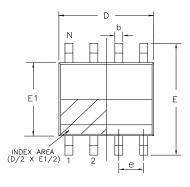
 0.75
 0.85
 0.95
 0.030
 0.033
 0.037
 A1 A2 0.015 0.22 — 0.38 0.009 b
 0.23
 0.003
 0.08 0.009 4.90 BSC 0.193 BSC 3.00 BSC 0.118 BSC E1 0.65 BSC 0.026 BSC 0.077 BSC 1.95 BSC 0.016 0.024 0.031 0.40 0.60 0.80 0.037 REF L1 0.95 REF 0.010 BSC L2 0.25 BSC 0.07 — — 0.003 — — 0.003 R1 0.07 0° — 8° 5° — 15° 0° - 8° 5° - 15° θ θ1 3.00 BSC 0.118 BSC

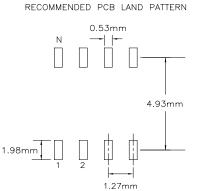


Front View

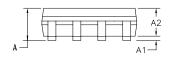
Mechanical Dimensions

SOIC-8 Package





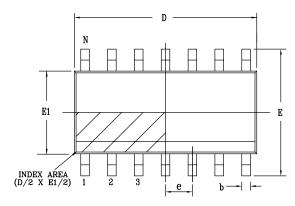
Top View



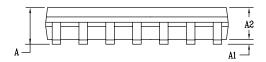
Side View

8 Pin	SOICN	JEDE	EC MS-	-012 '	√ariatio	n AA	
DIMENSIONS IN MM DIMENSIONS IN INCH							
SYMBOLS	(C	ontrol Un	it)	(Refe	(Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.35	_	1.75	0.053	_	0.069	
A1	0.10	_	0.25	0.004	_	0.010	
A2	1.25	_	1.65	0.049	_	0.065	
Ь	0.31	_	0.51	0.012	_	0.020	
С	0.17	_	0.25	0.007	_	0.010	
Е	(3.00 BSC		C	.236 BS	С	
E1		3.90 BSC		C	.154 BS	С	
е		1.27 BSC		C	.050 BS	С	
h	0.25	_	0.50	0.010	_	0.020	
L	0.40	_	1.27	0.016	_	0.050	
L1	1.04 REF			0	.041 REF		
L2	0.25 BSC			0	.010 BS0)	
R	0.07	_	_	0.003	_		
R1	0.07	_	_	0.003	_	_	
θ	0,	_	8°	0,	_	8,	
θ1	5°	_	15°	5°	_	15°	
θ2	0,	_	_	0,	_		
D	4.90 BSC 0.193 BSC				0		
N	8 8						

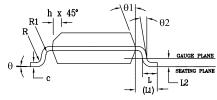
SOIC-14 Package



Top View



Side View

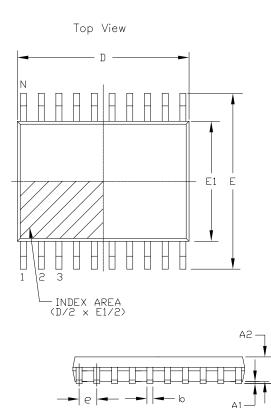


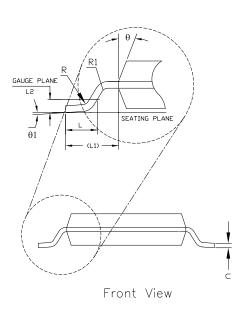
Front View

PACKAGE OUTLINE NSOIC .150" BODY JEDEC MS-012							
SYMBOLS		COMMON DIMENSIONS IN MM COMMON DIMENSIONS IN INCH (Control Unit) (Reference Unit)					
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.35		1.75	0.053	I	0.069	
A1	0.10	_	0.25	0.004		0.010	
A2	1.25	_	1.65	0.049	_	0.065	
b	0.31		0.51	0.012	_	0.020	
С	0.17	_	0.25	0.007	_	0.010	
E		6.00 BS0		- 0	.236 BS	c	
E1		3.90 BS0)	- 0	.154 BS	iC .	
е		1.27 BS0)	-	.050 BS	C	
h	0.25	_	0.50	0.010	_	0.020	
L	0.40	_	1.27	0.016	_	0.050	
L1		1.04 REF		0	.041 REF	F	
L2		0.25 BS0		0	.010 BS	2	
R	0.07	_	_	0.003	_	_	
R1	0.07	_	_	0.003	_	_	
θ	0,	_	8*	0,		8*	
θ1	5*	_	15°	5*	-	15°	
θ2	0,	_	_	0,	_	_	
D	SEE VARIATIONS						
N SEE VARIATIONS							

	VARIATION D							
WKWIIONO	VADIATI	DIMENSIONS IN MM (Control Unit)			DIMENSIONS IN INCH (Reference Unit)			N
2	SS S	MIN	NOM	MAX	MIN	NOM	MAX	
Α	Α	4.90 BSC			0.193 BSC			8
Α	В	8.65 BSC			0.341 BSC			14
Α	C	9.90 BSC			0	.390 BS	SC	16

TSSOP-14 Package





Side View

14 Pin TSSOP JEDEC MO-153 Variation AB-1						
SYMBOLS	DIMENSIONS IN MM (Control Unit)			DIMENSIONS IN INCH (Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX
Α	_		1.20	_	_	0.047
A1	0.05		0.15	0.002	_	0.006
A2	0.80	1.00	1.05	0.031	0.039	0.041
b	0.19	_	0.30	0.007	_	0.012
С	0.09	_	0.20	0.004	_	0.008
E	6.40 BSC			0.252 BSC		
E1	4.30	4.40	4.50	0.169	0.173	0.177
е	0.65 BSC			0.026 BSC		
L	0.45	0.60	0.75	0.018	0.024	0.030
L1	1.00 REF			0.039 REF		
L2	().25 BS	C	0.010 BSC		
R	0.09	_	_	0.035	_	_
R1	0.09	—	—	0.035	_	_
θ	12° REF			12° REF		
θ1	0,	_	8°	0,	_	8*
D	4.90	5.00	5.10	0.193	0.197	0.200
N	N 14			14		

Ordering Information

Part Number	Package	Green	Operating Temperature Range	Packaging	
CLC2011 Ordering Information					
CLC2011ISO8X	SOIC-8	Yes	-40°C to +125°C	Tape & Reel	
CLC2011ISO8MTR	SOIC-8	Yes	-40°C to +125°C	Mini Tape & Reel	
CLC2011ISO8EVB	Evaluation Board	N/A	N/A	N/A	
CLC2011IMP8X	MSOP-8	Yes	-40°C to +125°C	Tape & Reel	
CLC2011IMP8MTR	MSOP-8	Yes	-40°C to +125°C	Mini Tape & Reel	
CLC2011IMP8EVB	Evaluation Board	N/A	N/A	N/A	
CLC4011 Ordering Information					
CLC4011ISO14X	SOIC-14	Yes	-40°C to +125°C	Tape & Reel	
CLC4011ISO14MTR	SOIC-14	Yes	-40°C to +125°C	Mini Tape & Reel	
CLC4011ISO14EVB	Evaluation Board	N/A	N/A	N/A	
CLC4011ITP14X	TSSOP-14	Yes	-40°C to +125°C	Tape & Reel	
CLC4011ITP14MTR	TSSOP-14	Yes	-40°C to +125°C	Mini Tape & Reel	
CLC4011ITP14EVB	Evaluation Board	N/A	N/A	N/A	

Moisture sensitivity level for all parts is MSL-1. Mini tape and reel quantity is 250.

Revision History

Revision	Date	Description
1D (ECN 1504-01)	January 19, 2015	Reformat into Exar data sheet template. Updated PODs and thermal resistance numbers. Updated ordering information table to include MTR and EVB part numbers. Increased operating temperature to +125°C.
1D.R	July 2018	Updated to Resurgent Semiconductor.

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